



800V Super-Junction Power MOSFET

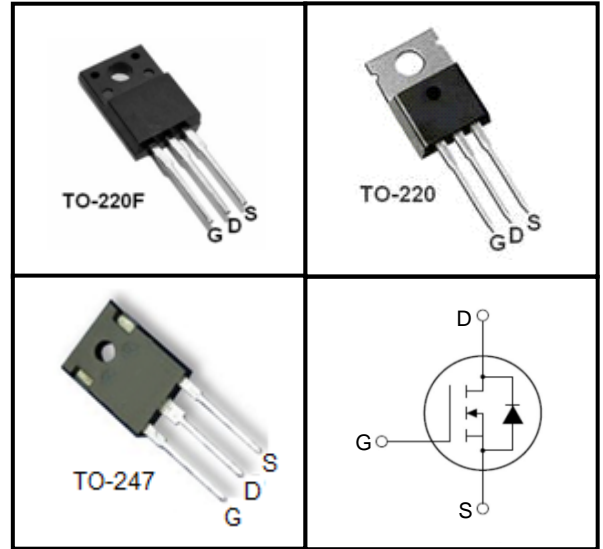
FEATURES

- Very low FOM $R_{DS(on)} \times Q_g$
- 100% avalanche tested
- RoHS compliant



APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information		
Device	Package	Marking
TPA80R250A	TO-220F	80R250A
TPP80R250A	TO-220	80R250A
TPW80R250A	TO-247	80R250A

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted				
Parameter	Symbol	Value		Unit
		TO-220F	TO-220, TO-247	
Drain-Source Voltage ($V_{GS} = 0\text{V}$)	V_{DSS}	800		V
Continuous Drain Current	I_D	$T_C = 25^\circ\text{C}$	18	A
		$T_C = 100^\circ\text{C}$	10.8	
Pulsed Drain Current (note1)	I_{DM}	54		A
Gate-Source Voltage	V_{GSS}	± 30		V
Single Pulse Avalanche Energy (note2)	E_{AS}	280		mJ
Avalanche Current (note1)	I_{AR}	7.5		A
Repetitive Avalanche Energy (note1)	E_{AR}	0.5		mJ
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	34	240	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150		$^\circ\text{C}$

Thermal Resistance				
Parameter	Symbol	Value		Unit
		TO-220F	TO-220, TO-247	
Thermal Resistance, Junction-to-Case	R_{thJC}	3.67	0.52	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	80	62	



Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	800	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 800V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	μA
		$V_{DS} = 800V, V_{GS} = 0V, T_J = 150^\circ\text{C}$	--	--	100	
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.5	--	4.5	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 9A$	--	0.24	0.28	Ω
Forward Transconductance (Note3)	g_{fs}	$V_{DS} = 10V, I_D = 9A$	--	10	--	S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = 50V,$ $f = 1.0\text{MHz}$	--	3871	--	μF
Output Capacitance	C_{oss}		--	217	--	
Reverse Transfer Capacitance	C_{rss}		--	17.1	--	
Total Gate Charge	Q_g	$V_{DD} = 640V, I_D = 18A,$ $V_{GS} = 10V$	--	62.3	--	nC
Gate-Source Charge	Q_{gs}		--	14.5	--	
Gate-Drain Charge	Q_{gd}		--	23	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 400V, I_D = 9A,$ $R_G = 25\Omega$	--	49	--	ns
Turn-on Rise Time	t_r		--	42.6	--	
Turn-off Delay Time	$t_{d(off)}$		--	166	--	
Turn-off Fall Time	t_f		--	13	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^\circ\text{C}$	--	--	18	A
Pulsed Diode Forward Current	I_{SM}		--	--	54	
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{SD} = 18A, V_{GS} = 0V$	--	0.9	1.2	V
Reverse Recovery Time	t_{rr}	$V_R = 400V, I_F = I_S,$ $di_F/dt = 100A/\mu s$	--	400	--	ns
Reverse Recovery Charge	Q_{rr}		--	4	--	μC
Peak Reverse Recovery Current	I_{rrm}		--	20	--	A

Notes

1. Repetitive Rating: Pulse Width limited by maximum junction temperature
2. $I_{AS} = 7.5A, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 1\%$



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

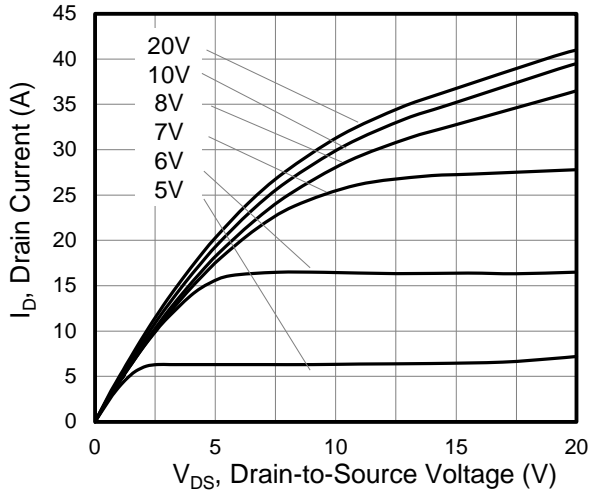


Figure 2. Transfer Characteristics

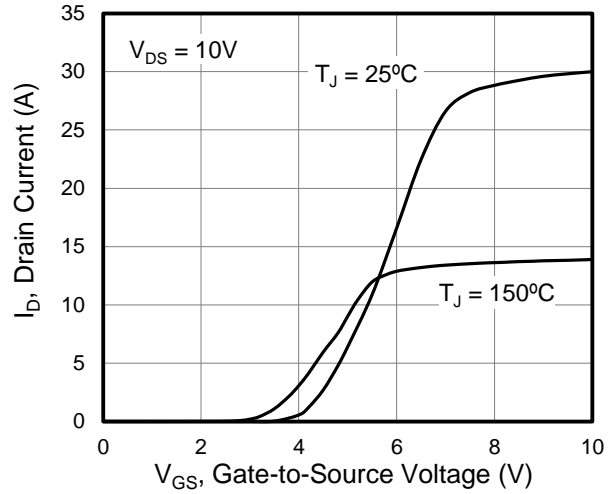


Figure 3. On-Resistance vs. Drain Current

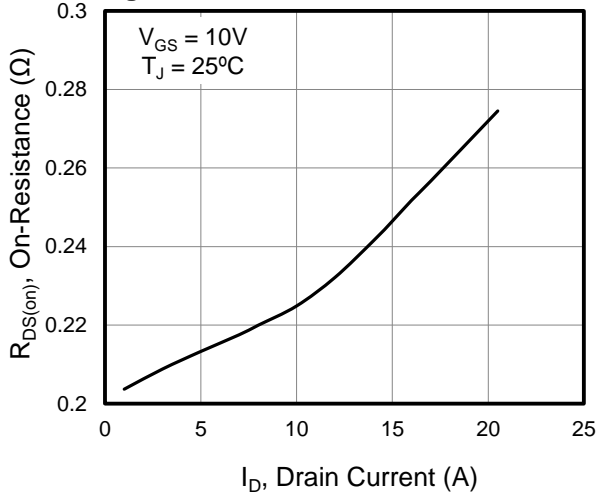


Figure 4. Capacitance

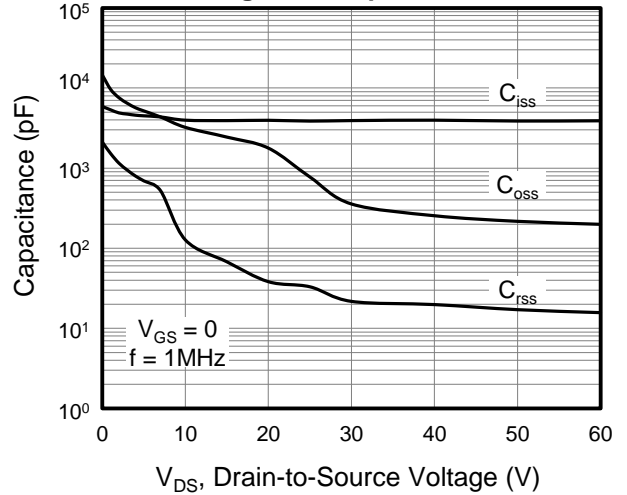


Figure 5. Gate Charge

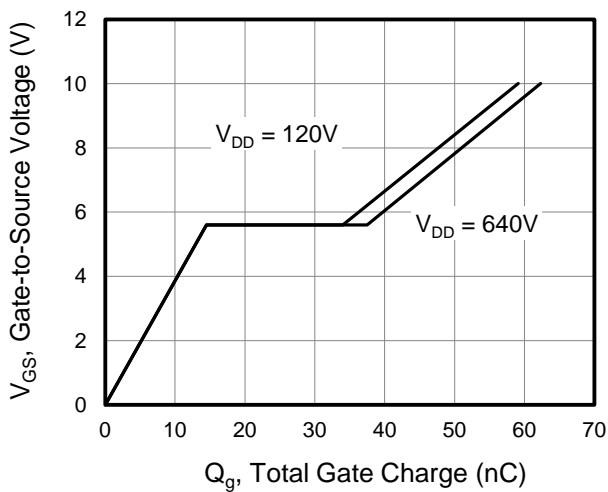
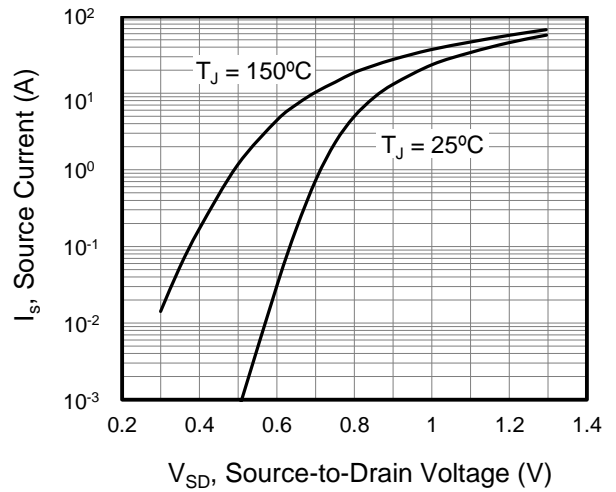


Figure 6. Body Diode Forward Voltage





Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. On-Resistance vs. Junction Temperature

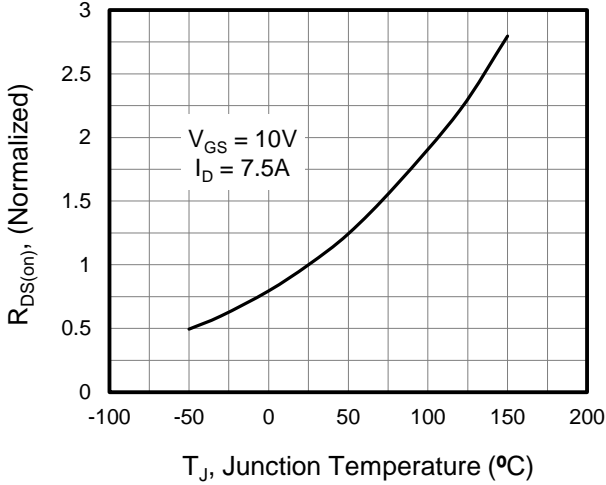


Figure 8. Breakdown voltage vs. Junction Temperature

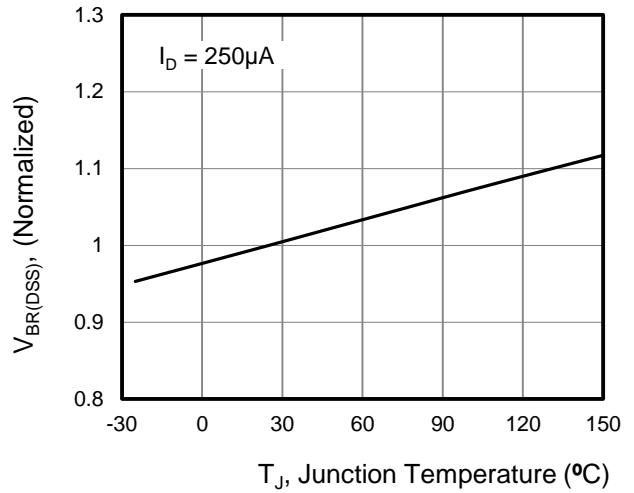


Figure 9. Transient Thermal Impedance TO-220F

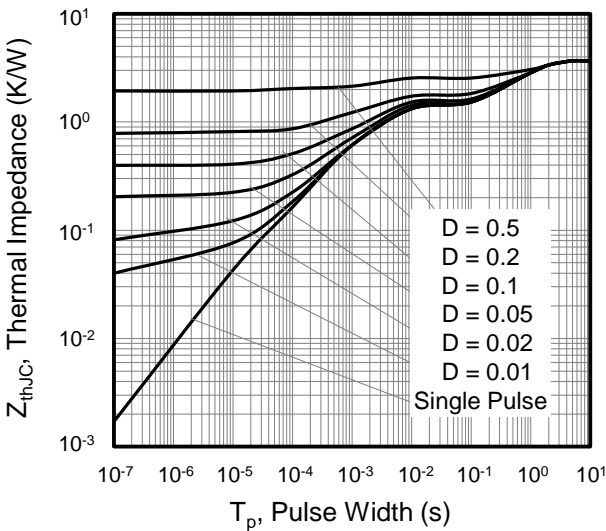


Figure 9. Transient Thermal Impedance TO-220,TO-247

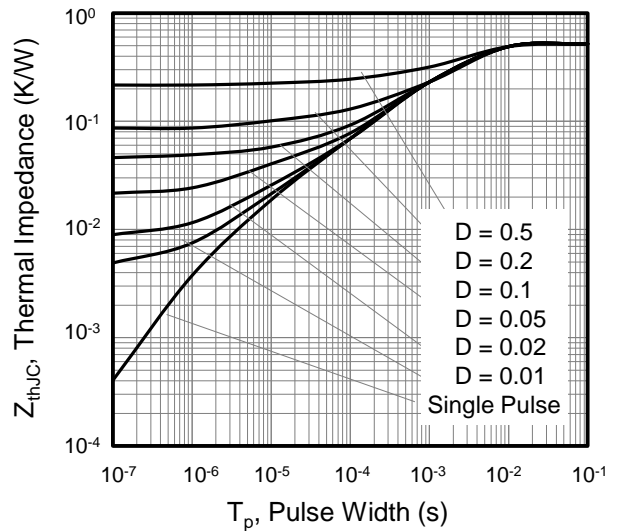


Figure 13. Safe operation area for TO-220F

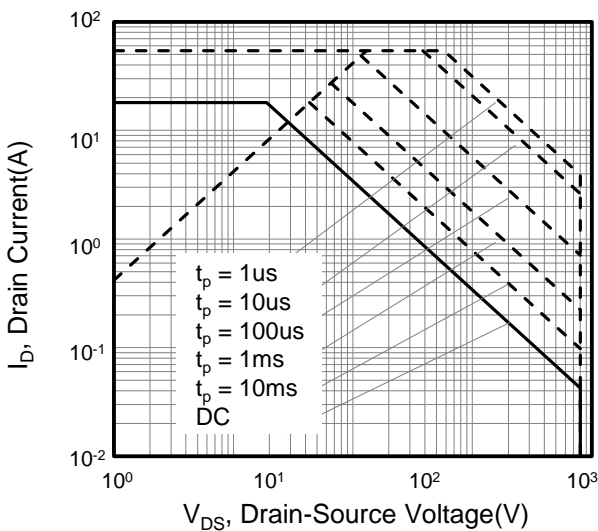


Figure 12. Safe operation area for TO-220,TO-247

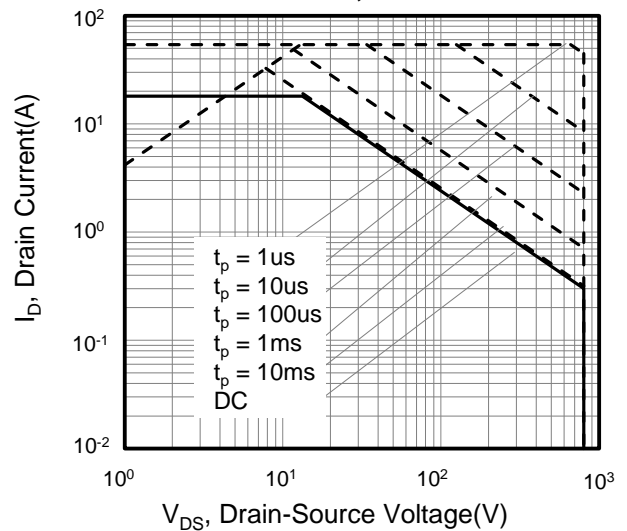




Figure A: Gate Charge Test Circuit and Waveform



Figure B: Resistive Switching Test Circuit and Waveform

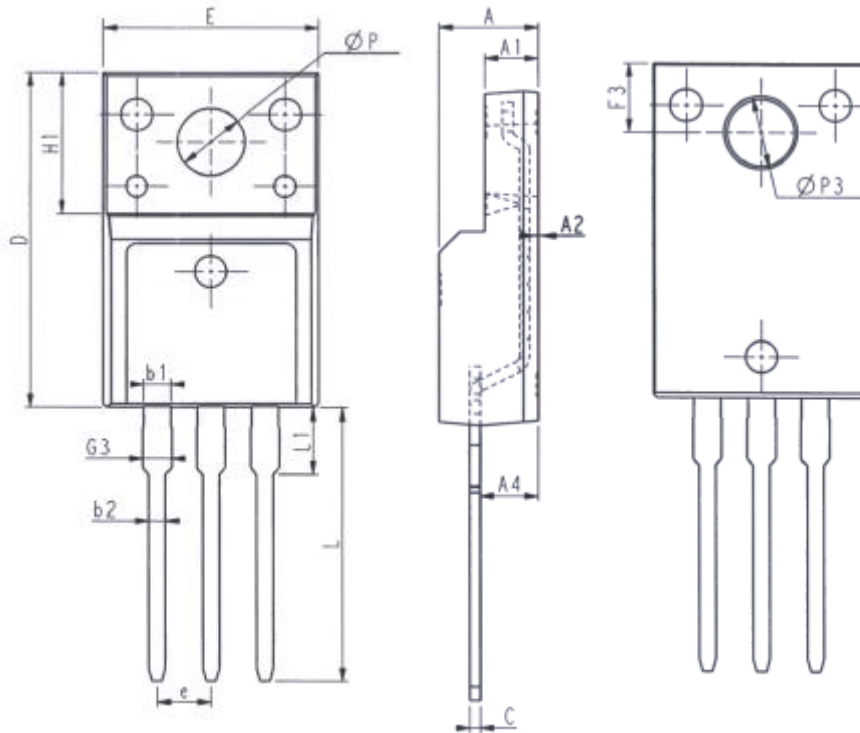


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





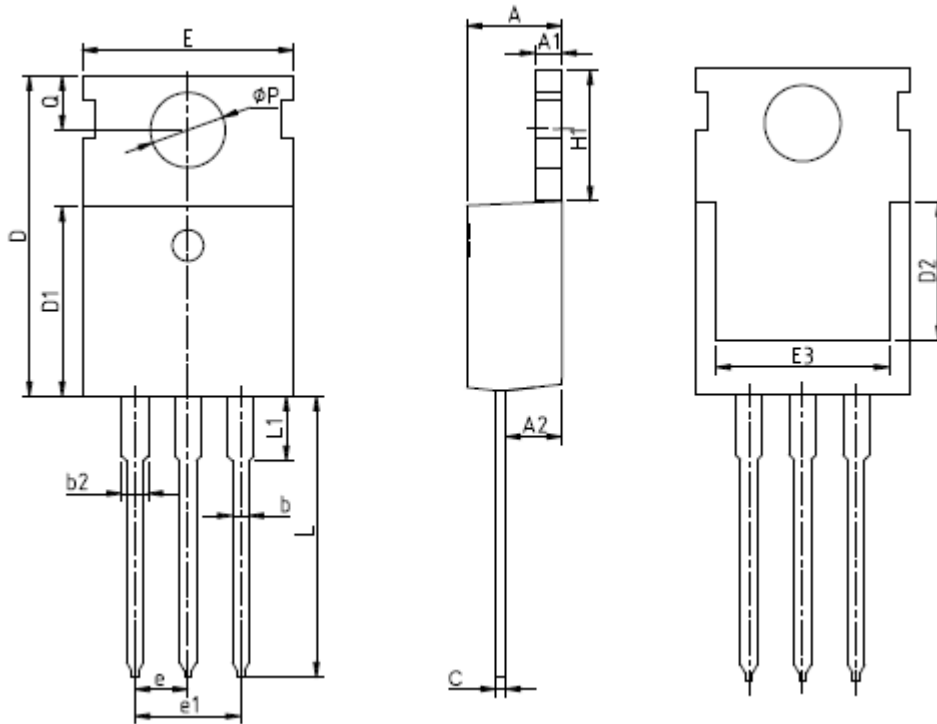
TO-220F



SYMBOL	MM		
	MIN	NOM	MAX
E	9.96	10.16	10.36
A	4.50	4.70	4.90
A1	2.34	2.54	2.74
A2	0.30	0.45	0.60
A4	2.56	2.76	2.96
c	0.40	0.50	0.65
c1	1.20	1.30	1.35
D	15.57	15.87	16.17
H1	6.70REF		
e	2.54BSC		
L	12.68	12.98	13.28
L1	2.93	3.03	3.13
ΦP	3.03	3.18	3.38
$\Phi P3$	3.15	3.45	3.65
F3	3.15	3.30	3.45
G3	1.25	1.35	1.55
b1	1.18	1.28	1.43
b2	0.70	0.80	0.95



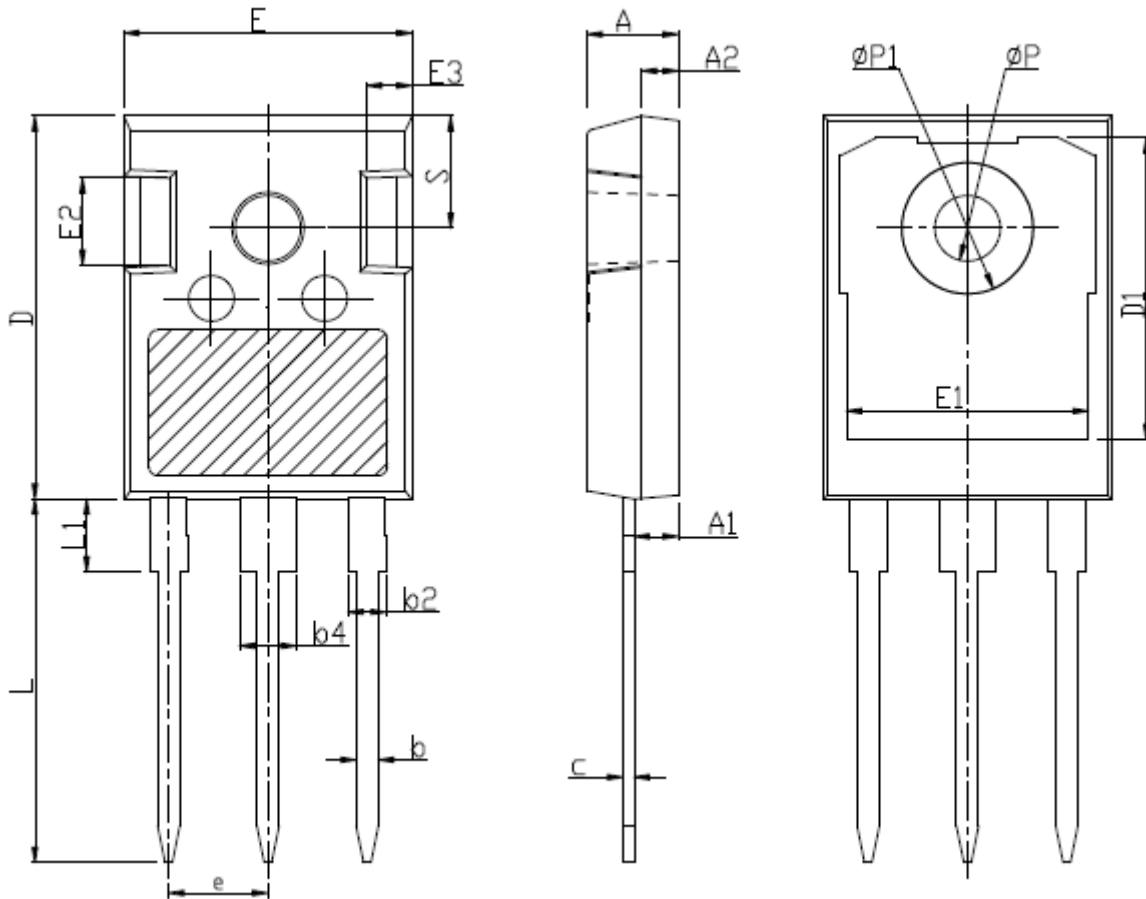
TO-220



SYMBOL	MIN	NOM	MAX
A	4.37	4.57	4.70
A1	1.25	1.30	1.40
A2	2.20	2.40	2.60
b	0.70	0.80	0.95
b2	1.17	1.27	1.47
c	0.45	0.50	0.60
D	15.10	15.60	16.10
D1	8.80	9.10	9.40
D2	5.50	-	-
E	9.70	10.00	10.30
E3	7.00	-	-
e	2.54 BSC		
e1	5.08 BSC		
H1	6.25	6.50	6.85
L	12.75	13.50	13.80
L1	-	3.10	3.40
ϕP	3.40	3.60	3.80
Q	2.60	2.80	3.00



TO-247



SYMBOL	mm		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.21	2.41	2.59
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
b4	2.91	3.01	3.21
c	0.51	0.61	0.75
D	20.80	21.00	21.30
D1	16.25	16.55	16.85
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.20
E3	2.30	2.50	2.70
e	5.44BSC		
L	19.62	19.92	20.22
L1	-	-	4.30
ΦP	3.40	3.60	3.80
ΦP1	-	-	7.30
S	6.15BSC		



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